

## Supporting Information

### Silicon-nanoforest-based Solvent-free Micro-supercapacitor with Ultrahigh Spatial Resolution via IC-compatible *In-situ* Fabrication for On- chip Energy Storage

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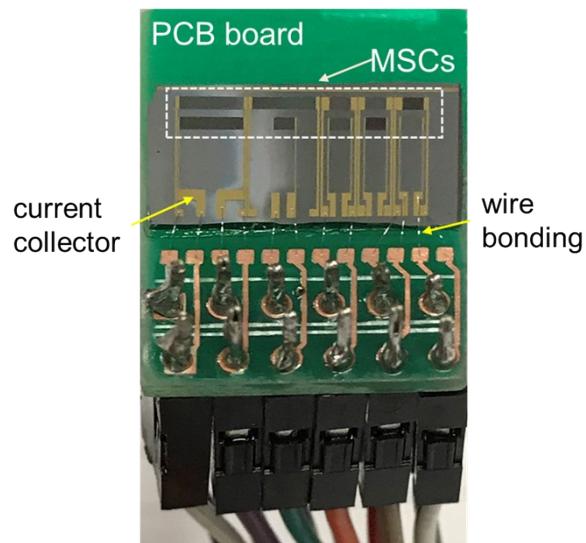


Figure S1. A home-made solid-state on-chip SNNF-MSC test setup.

**Measurement setup:** One batch of MSCs were cut from a Si wafer with about 500 samples and assembled with a home-built PCB board (green colour), as shown in Figure S1. The current collectors of each MSCs were connected to the PCB board conducting pads through the wire-bonding method. After welding, the MSCs were successfully connected with the corresponding external circuit for testing.

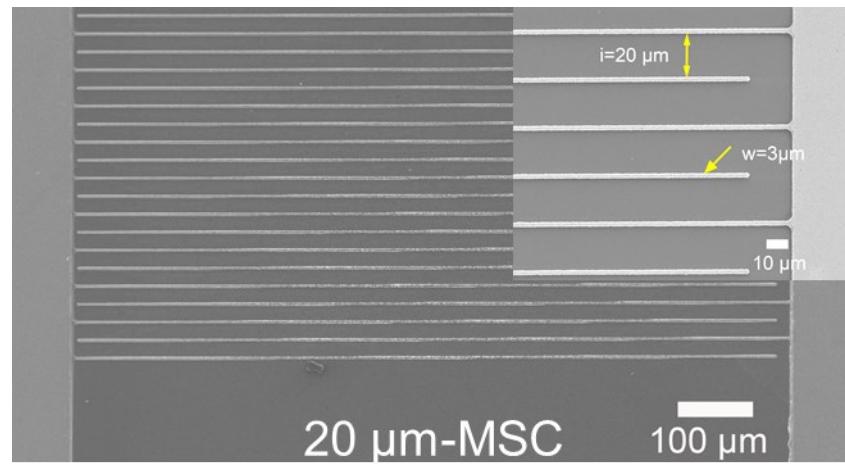


Figure S2. Top-view SEM image of 20  $\mu$ m MSC

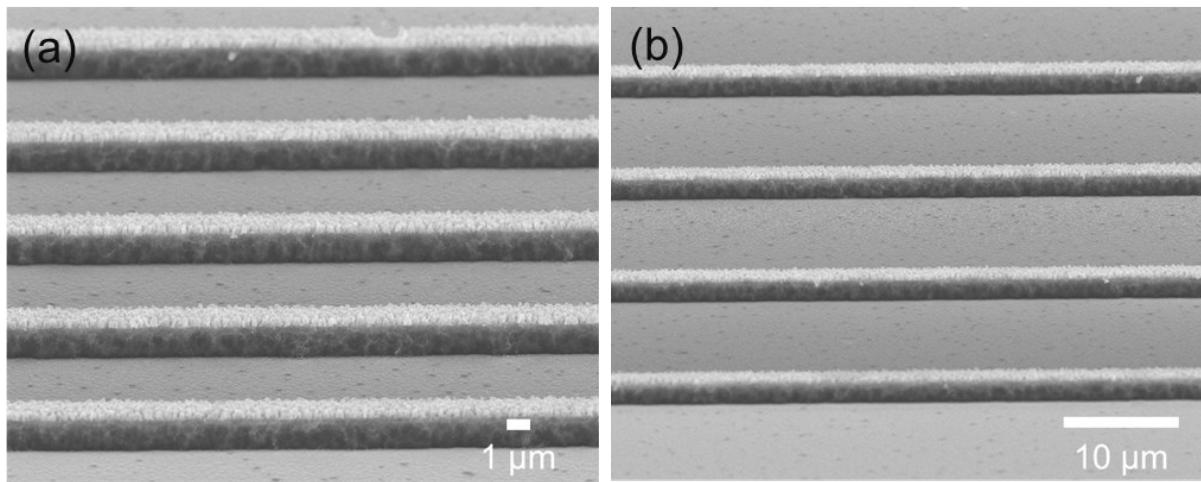


Figure S3. 45-degree-view SEM images of silicon-pillar nanoforest structure of (a) 10- $\mu\text{m}$ -MSC and (b) 20- $\mu\text{m}$ -MSC on a silicon chip.

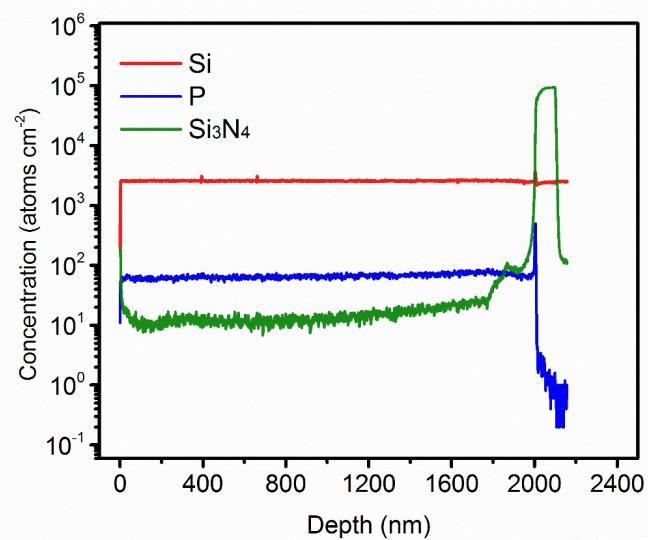


Figure S4. SIMS measurement result of phosphorus-doped n-type silicon.

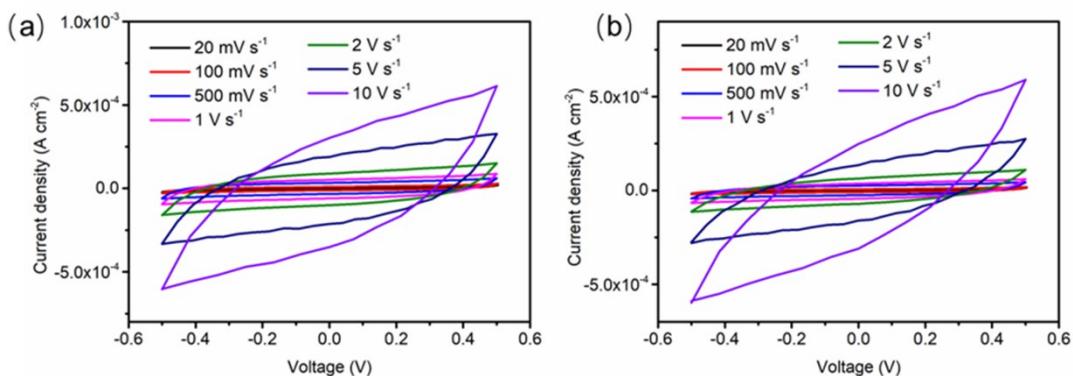


Figure S5. CV curves of (a)  $10\mu\text{m}$ -MSCs and (b)  $20\mu\text{m}$ -MSCs at various scan rates  $20\text{ mV s}^{-1}$  to  $10\text{ V s}^{-1}$ .

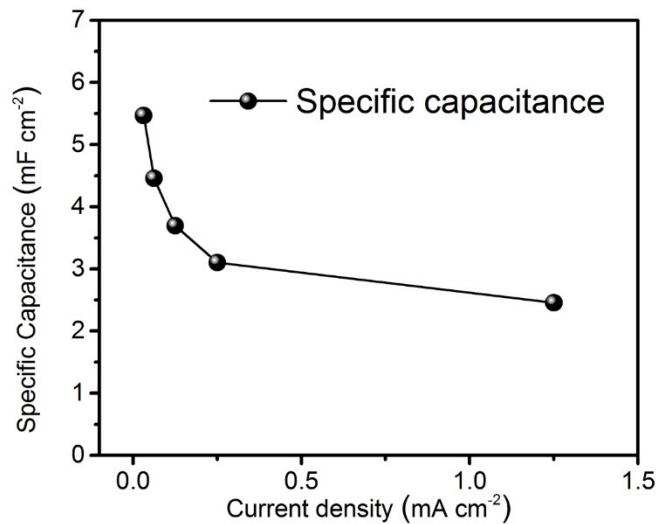


Figure S6. The specific capacitance of  $5\text{-}\mu\text{m}$ -MSC at various charge-discharge current densities from  $0.03\text{ mA cm}^{-2}$  to  $1.25\text{ mA cm}^{-2}$ .

Table S1. Comparison of the spatial resolution and responding performance with recent MSCs made by different techniques.

Electrode	Method	Width /μm	Gap /μm	Time consta nt	Capacitance /mF cm <sup>-2</sup>	Energy density/ mWh cm <sup>-3</sup>	Power density/ W cm <sup>-3</sup>	Ref.
/ms								
rGO/Au	Laser written	140	60	2.76	0.77 @ 1V s <sup>-1</sup>	/	/	1
LSG-MSC	Laser- scribed	~20	~20	19	2.32 @ 16.8 mA cm <sup>-3</sup>	0.3	10	2
Ti3C2Tx	Laser	1800	284	/	0.47 @ 1.0 μA cm <sup>-2</sup>	0.53	11.96	3
Mxene	cutting							
Mxene	Laser cutting	109.2	598.6	/	19.6 @ 20 mV s <sup>-1</sup>	18	0.7	4
Activated carbon	Jet printing	~10	<50	/	0.127 @ 1 mV s <sup>-1</sup>	/	/	5
Graphene	Inkjet printing	600	300	2000	0.14 @ 5 mV s <sup>-1</sup>	/	/	6
Si/TiC/CDC	Photolith ography	100	15	/	400 F cm <sup>-3</sup> @ 1 mV s <sup>-1</sup>	9	0.5	7
PEDOT/Au	Photolith ography	100	50	10	9 @ 35 μA cm <sup>-2</sup>	7.7	0.8	8
MnOx/Au	Photolith ography	100	100	5	32.8 F cm <sup>-3</sup>	1.75	3.4	9
Si	Photolith ography	200	200	/	0.013 @ 100 mV s <sup>-1</sup>	/	/	10
Si/Ni	Photolith ography	3	5	1.09	0.238 @ 1.25 mA cm <sup>-2</sup>	0.15	4.15	This work

## References

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